

4. (Once Amended) The semiconductor device as cited in Claim 1, wherein said cobalt including layer [being] is formed on a copper wiring [face].

5. (Once Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a cobalt including layer on a conductive member; and

forming a cobalt silicide layer on [said] a surface of the cobalt including layer.

6. (Once Amended) The method as cited in claim 5, wherein said cobalt silicide layer [being] is formed by exposing said cobalt including layer in a silane system gas.

Please add the following new claims:

8. A semiconductor device comprising:

a conductive member;

a layer of CoWP formed over the conductive member; and

a layer of cobalt silicide formed over the layer of CoWP.

9. The semiconductor device of claim 8, wherein the conductive member is a copper wiring.

10. The method of claim 5, wherein the cobalt including layer is a layer comprised of CoWP.